

Title (en)

METHOD OF PRODUCING RELAXED SILICON GERMANIUM LAYERS

Title (de)

METHODE ZUR HERSTELLUNG RELAXIERTER SILIZIUM-GERMANIUM-SCHICHTEN

Title (fr)

PROCEDE DE PRODUCTION DE COUCHES DE SILICIUM-GERMANIUM DECONTRACTEES

Publication

EP 1214735 A1 20020619 (EN)

Application

EP 00974128 A 20000919

Priority

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Abstract (en)

[origin: WO0122482A1] A method for making a semiconductor material, and subsequent structure, including providing a monocrystalline silicon substrate; epitaxially growing, using a source gas of GexHyClz for the germanium component, on the silicon substrate at a temperature in excess of 850 DEG C a graded Si1-xGex layer with increasing germanium concentration at a gradient of less than 25 % Ge per micron to a final composition in the range of 0.1<=x<=1; and epitaxially growing a layer of semiconductor material on the graded layer.

IPC 1-7

H01L 21/20

IPC 8 full level

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